



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No.: Q61743

Takashi UDAGAWA

Appln. No.: 09/885,943

Group Art Unit: 2826

Confirmation No.: 6215

Examiner: Johannes P. Mondt

Filed: June 22, 2001

For: GROUP-III NITRIDE SEMICONDUCTOR  
LIGHT-EMITTING DEVICE AND  
PRODUCTION METHOD THEREOF

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated June 5, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 2, 3, 6-9, and 13 without prejudice or disclaimer.

Please enter the following amended claim:

Sub B

1. (Amended) A group-III nitride semiconductor light-emitting device comprising a single crystal substrate having thereon a light-emitting part structure comprising a gallium nitride phosphide ( $GaN_{1-x}P_x$ , wherein  $0 < x < 1$ ) single crystal layer provided via a boron phosphide (BP)-based buffer layer, wherein the boron phosphide-based buffer layer comprises a multilayer structure including an amorphous layer and a crystalline layer formed on the amorphous layer, both the amorphous layer and the crystalline layer being made of the same material.

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